

# Intrinsic Resistance Switching in Amorphous Silicon Suboxides: The Role of Columnar Microstructure

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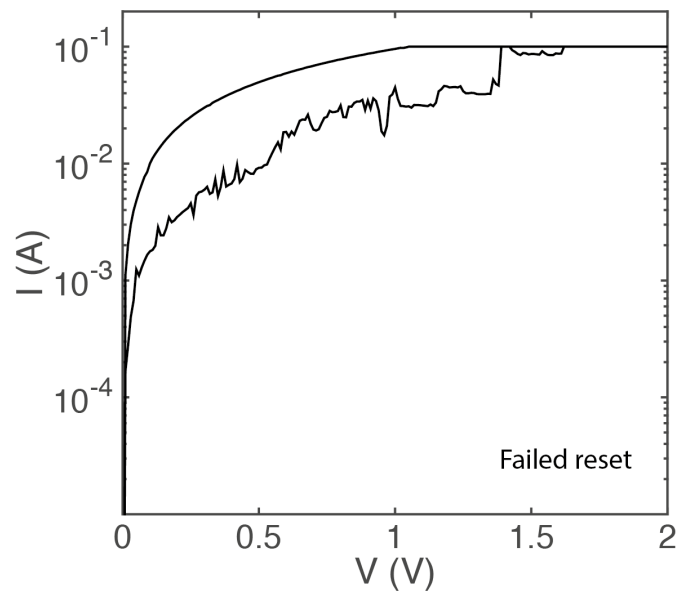
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## Supplementary Information



**Figure S1.** Example of a failed reset operation for a type 3c device after initial electroforming.